

Fig. 1(B)  
ENLARGED DIAGRAM OF 105

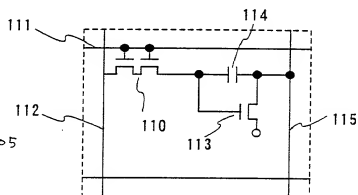
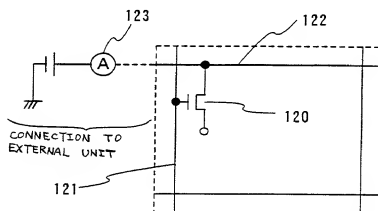


Fig. 1(C)  
ENLARGED  
DIAGRAM OF 106



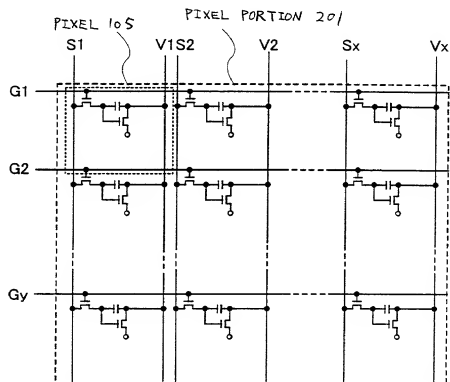


Fig. 2(A)

OPPOSING PORTION 106

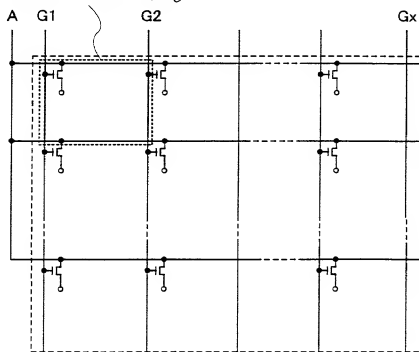
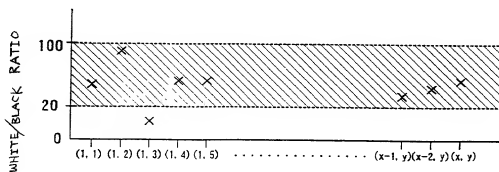


Fig. 2(B)

Fig. 3(A)

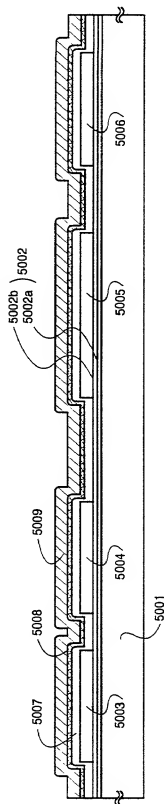
(1, 1)	(2, 1)	(3, 1)	(4, 1)		(x-1, 1)	(x, 1)
(1, 2)	(2, 2)	(3, 2)	(4, 2)		(x-1, 2)	(x, 2)
(1, 3)	(2, 3)	(3, 3)	(4, 3)		(x-1, 3)	(x, 3)
(1, 4)	(2, 4)	(3, 4)	(4, 4)		(x-1, 4)	(x, 4)
(1, y-1)	(2, y-1)	(3, y-1)	(4, y-1)		(x-1, y-1)	(x, y-1)
(1, y)	(2, y)	(3, y)	(4, y)		(x-1, y)	(x, y)

Fig. 3(B)



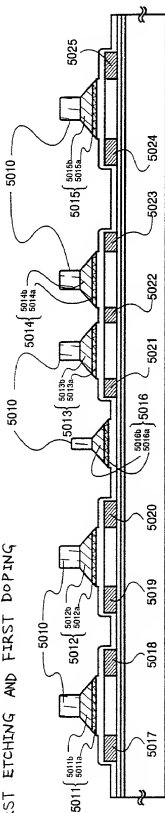
FORMATION OF ISLAND SEMICONDUCTOR LAYER, GATE-INSULATING FILM,  
AND FIRST AND SECOND CONDUCTING FILMS FOR GATE ELECTRODES

Fig. 4(A)



FIRST ETCHING AND FIRST DOPING

Fig. 4(B)



SECOND ETCHING

Fig. 4(C)

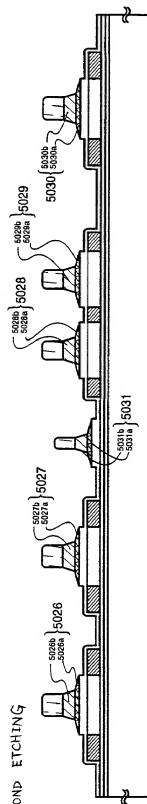


Fig. 5(A) SECOND DOPING

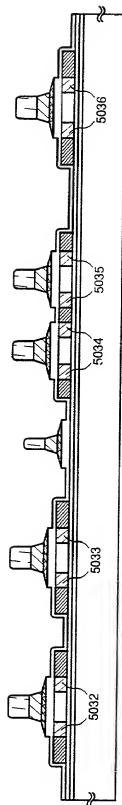


Fig. 5(B) THIRD ETCHING

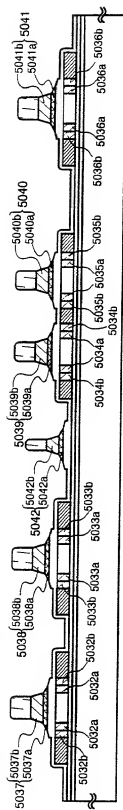
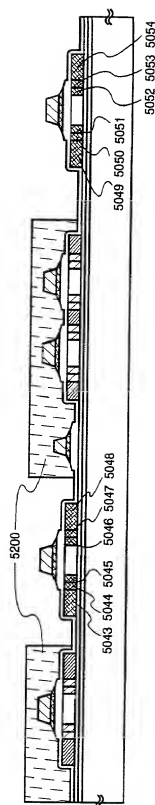
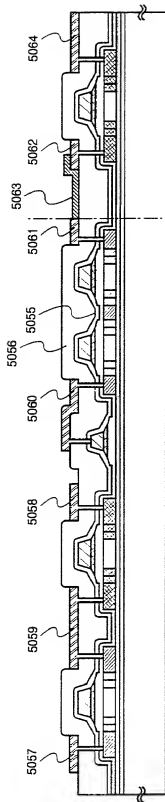


Fig. 5(C) THIRD DOPING



FORMATION OF THE FIRST AND SECOND INTERLAYER-INSULATING FILMS,  
WIRINGS AND PIXEL ELECTRODES

Fig. 6(A)



FORMATION OF THE THIRD INTERLAYER-INSULATING FILM, EL LAYER,  
CATHODES AND PASSIVATION FILM

Fig. 6(B)

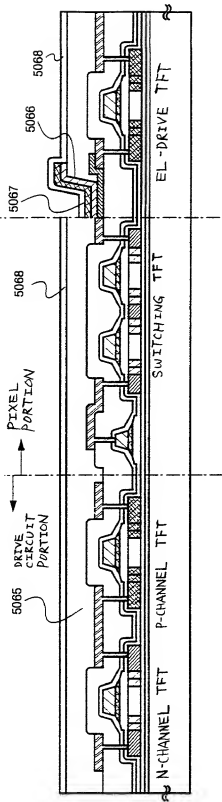


Fig. 7(A)

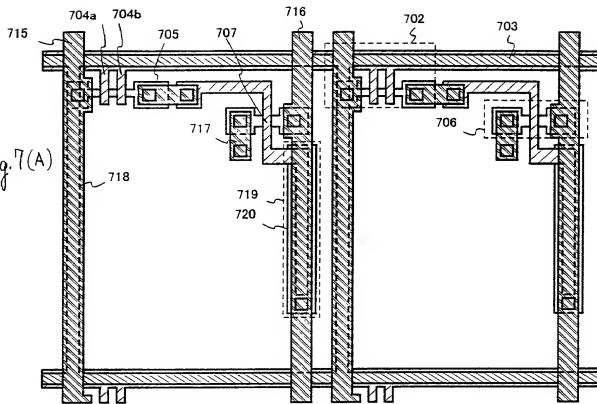
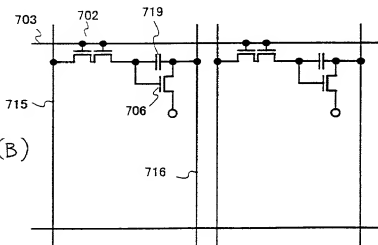
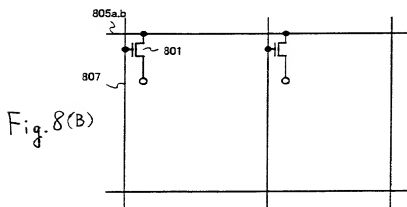
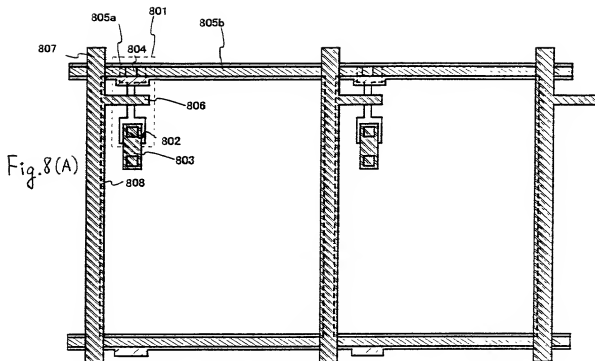


Fig. 7(B)





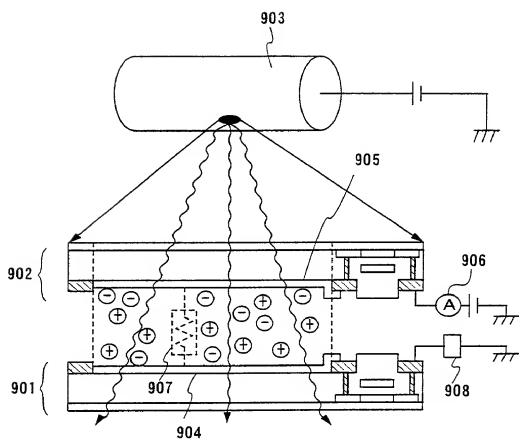


Fig. 9

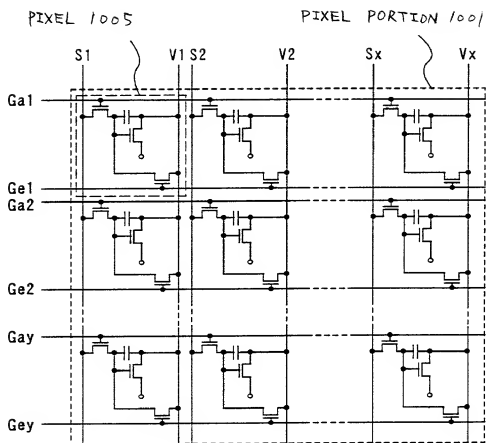


Fig. 10

SOURCE OF ELECTROMAGNETIC  
WAVES 1101

POWER SOURCE 1104

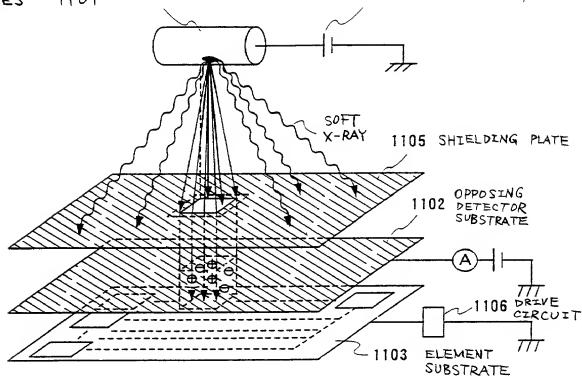


Fig. 11

SOURCE OF ELECTROMAGNETIC WAVES

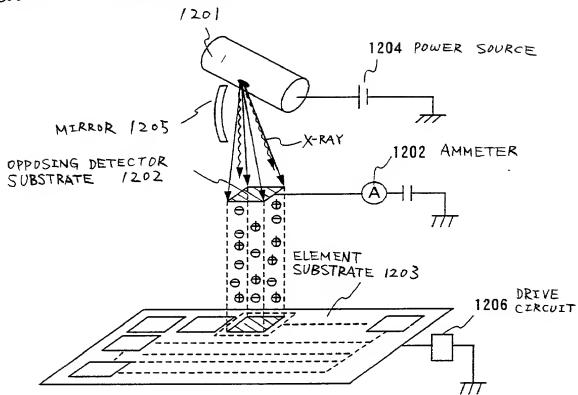


Fig.12

Fig. 13(A)

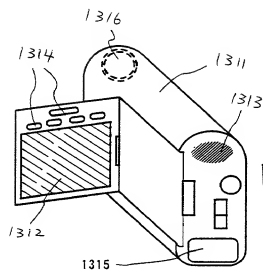
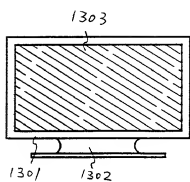


Fig. 13(B)

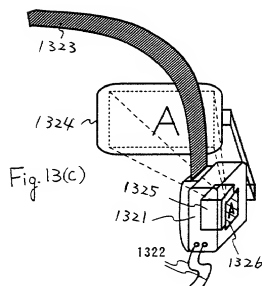


Fig. 13(C)

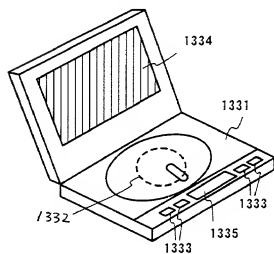


Fig. 13(D)

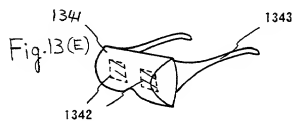


Fig. 13(E)

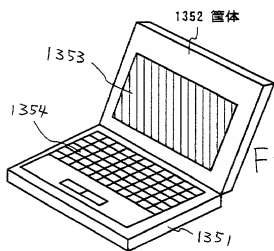


Fig. 13(F)

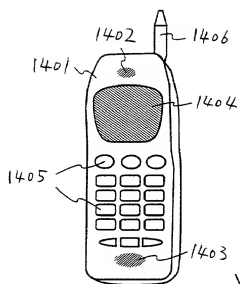


Fig. 14(A)

Fig. 14(B)

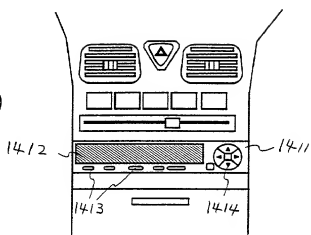


Fig. 14(C)

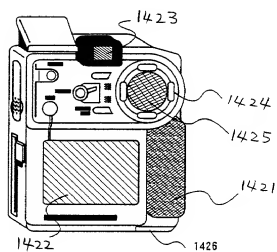


Fig. 15

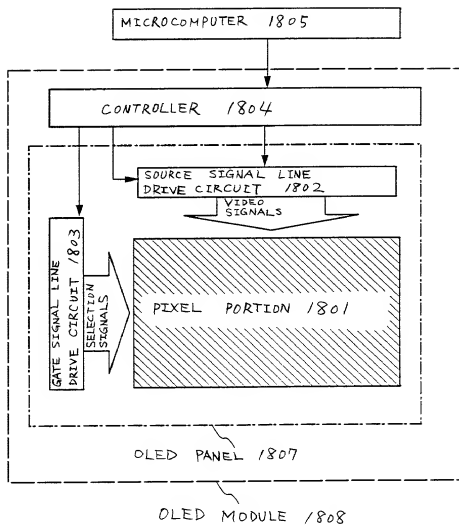


Fig. 16(A)

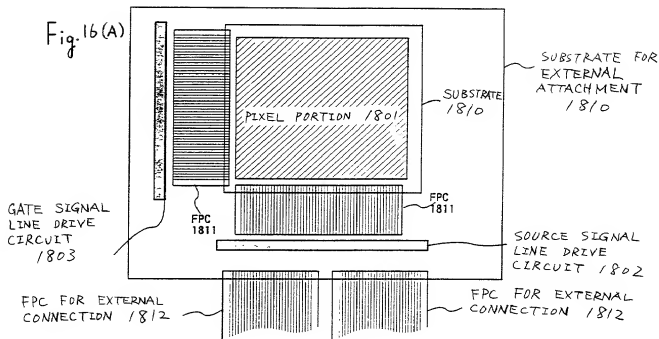


Fig. 16(B)

